





ead-free Gre

ZXTP26020DMF

20V LOW $V_{CE(SAT)}$ PNP SURFACE MOUNTED TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (ZXTN26020DMF)
- Low Collector-Emitter Saturation Voltage, V_{CE(SAT)}
- High Current Gain (h_{FE}) at High I_C
- Surface Mount Package Suited for Automated Assembly
- Ultra-Small Surface Mount Package
- Qualified to AEC-Q101 Standards for High Reliability
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM

Mechanical Data

- Case: DFN1411-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (approximate)

Applications

- MOSFET and IGBT gate driving
- DC-DC conversion
- Interface between low voltage IC and Load
- Load disconnect switch



Top view



Bottom view





Pin-Out Top view

Ordering Information

Product Reel size (inches) Tape width (mm) Quantity pe	r reel
ZXTP26020DMFTA 7 8 3000	

Notes: 1. No purposefully added lead. Halogen and Antimony Free.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



Z2= Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2009		2010	2011		2012	2013		2014	2015		2016
Code	W		Х	Y		Z	A		В	С		D
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D





Maximum Ratings

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	lc	-1.25	А
Peak Pulse Current	I _{CM}	-4	А
Base Current(DC)	IB	-0.3	А
Peak Base Current	I _{BM}	-0.6	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	PD	1	W
Power Dissipation (Note 4)	PD	380	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{ ext{ heta}JA}$	125	°C/W
Thermal Resistance, Junction to Ambient (Note 4) @ $T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	330	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	۵°

Notes:

Device mounted on FR-4 PCB with 1inch square pads.
Device mounted on FR-4 PCB with minimum recommended pad layout



Electrical Characteristics (at T_A = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-20	_	_	V	$I_{C} = -100 \mu A, I_{E} = 0A$
Collector-Emitter Breakdown Voltage (Note 5)	V _{(BR)CEO}	-20	—		V	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0 {\rm A}$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-7	_	_	V	$I_{E} = -100 \mu A, I_{C} = 0A$
Collector Cutoff Current	lcbo	_	_	-100 -0.5	nA μA	V _{CB} = -20V, I _E = 0A V _{CB} = -20V, I _E = 0A,T _A = 125°C
Emitter Cutoff Current	lces	_	_	-100	nA	$V_{CE} = -20V, V_{BE} = 0V$
Base Cutoff Current	lebo	_	_	-50	nA	$V_{BE} = -6V, I_{C} = 0A$
DC Current Gain (Note 5)	h _{FE}	300 235 175 140			_	$V_{CE} = -2V, I_C = -100mA$ $V_{CE} = -2V, I_C = -0.5A$ $V_{CE} = -2V, I_C = -1A$ $V_{CE} = -2V, I_C = -1.5A$
Collector-Emitter Saturation Voltage (Note 5)	V _{CE(SAT)}	 		-80 -100 -155 -235	mV mV mV mV	$\begin{split} I_{C} &= -100 \text{mA}, \ I_{B} &= -1 \text{mA} \\ I_{C} &= -500 \text{mA}, \ I_{B} &= -50 \text{mA} \\ I_{C} &= -1A, \ I_{B} &= -50 \text{mA} \\ I_{C} &= -1.25A, \ I_{B} &= -62.5 \text{mA} \end{split}$
Equivalent On-Resistance	R _{CE(SAT)}	_	125	_	mΩ	I _C = -1A, I _B = -50mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	—	—	-1.1	V	$V_{CE} = -5V, I_C = -1A$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-1.15	V	I _C = -1A, I _B = -50mA
Output Capacitance (Note 5)	C _{obo}	—	_	20	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	fT	200	_	_	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Turn-On Time	t _{on}		60	_	ns	
Delay Time	t _d	—	20	—	ns	
Rise Time	tr	—	40		ns	$V_{CC} = -10V, I_{C} = -1A$
Turn-Off Time	t _{off}	—	167	—	ns	$I_{B2} = -I_{B1} = -50 \text{mA}$
Storage Time	ts		140	—	ns	1
Fall Time	t _f	—	27		ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.













Package Outline Dimensions



DFN1411-3						
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0	0.05	0.02			
b	0.25	0.35	0.30			
D	1.35	1.475	1.40			
D2	0.65	0.85	0.75			
Е	1.05	1.18	1.10			
E2	0.65	0.85	0.75			
е			0.55			
L	0.225	0.325	0.275			
L1			0.20			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.38
G1	0.15
G2	0.15
Х	0.95
X1	0.75
X2	0.40
Ŷ	0.75
C	0.76



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